#4/IDS Review 10-29-01

Form PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.	SERIAL NO.
MI22-1568	09/879,335
APPLICANT Vishnu K. Agarwal, et al.	
FILING DATE June 11, 2001	GROUP 2813

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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	AB	3,571,914	03/1971	Lands, et al.			
	AC	4,464,701	08/1984	Roberts et al.			
	AD	5,504,041	04/1996	Summerfelt			
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	AG	5,663,088	09/1997	Sandhu et. al.			
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	AK	5,854,107	12/1998	Park et al.			
	AL	5,622,883	04/1997	Kim			

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	AN							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AO		Kamiyama, Satoshi et al., "Ultrathin Tantalum Oxide Capacitor Dielectric Layers Fabricated Using Rapid Thermal Nitridation Prior to Low Pressure Chemical Vapor Deposition: J. Electrochem. Soc., Vol. 140, #6, pp 1618-25 (6/1993)
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	AQ		Kamiyama, S., et al., Highly Reliable 2.5 nm Ta_2O_5 Capacitor Process Technology for 256 Mbit DRAMs", *IEEE*, pp. 827-830 (9/1991)
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EXAMINER [signature] DATE CONSIDERED 3/18/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

08/879,335

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ATTY. DOCKET NO.	SERIAL NO.
M122-1568	09/879,335
APPLICANT: Kunal R. Parekh, et al.	
FILING DATE: June 11, 2001	GROUP: 2813

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,597,756	01/1997	Fazan et al.			
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